

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device comprising:
a semiconductive layer of a first conductive type;
a first gate oxide film and a second gate oxide film formed on the semiconductive layer;
~~provided with a gate electrode formed so that the gate electrode ranges to range from at the~~
~~first gate oxide film formed on a first conductive type of semiconductor layer to at the~~ second gate
~~oxide film;~~ a second conductive type of
a source region of a second conductive type ~~formed so that the source region is adjacent~~
~~to the gate electrode;~~
~~a second conductive type of drain region~~ of a second conductive type ~~formed in a~~
~~position apart from the gate electrode; and~~
~~a second conductive type of a drift region~~ of a second conductive type ~~formed so that the~~
~~drift region surrounds the drain region; and, wherein:~~
~~a second conductive type of an~~ impurities layer of a second conductive type ~~is formed so~~
~~that it is adjacent to the drain region.~~

2. (Currently Amended) A semiconductor device according to Claim 1, wherein:
~~said second conductive type of impurities layer is formed so that it ranges to range~~ at least
~~from one end of the drain region to one end of the gate electrode.~~

3. (Currently Amended) A semiconductor device according to Claim 2, wherein:
~~said second conductive type of impurities layer is formed in a surface of the drift region~~
~~so that it is located between one end of the drain region and one end of the gate electrode.~~

Claims 4 to 6 canceled.

7. (Currently Amended) A semiconductor device comprising:

a gate electrode formed on a semiconductor layer of a first conduction type through a gate oxide film;

a highly doped source region of a second conduction type formed to be adjacent to the gate electrode,

a highly doped drain region of the second conduction type formed at a position apart from said gate electrode; and

a drift region of the second conduction type formed so as to surround said drain region;

wherein an impurity region of the second conduction type which is more lightly doped than said highly doped drain region and it is more highly doped than said drift region is formed so as to surround the a vicinity of said highly doped drain region.

8. (Currently Amended) A semiconductor device according to claim 1, further comprising:

a semiconductor layer of a first conduction type;

a first gate oxide film and a second gate oxide film formed on the semiconductor layer;

a gate electrode formed to extend from at the first gate oxide film ~~formed a semiconductor layer of the first conduction type onto~~ to the second gate oxide film having a larger thickness than that of said first gate oxide film;

a source region of a second conduction type formed to be adjacent to the gate electrode;

a drain region of the second conduction type formed at a position apart from said gate electrode; and

a drift region of the second conduction type formed so as to surround said drain region.

~~W~~wherein an impurity region of the second conduction type which is more lightly doped than said drain region and is more highly doped than said drift region is formed so as to surround the vicinity of said highly doped drain region.

9. (Original) A semiconductor device according to claim 8, wherein said impurity region of the second conduction type is formed to extend from at least one end of said drain region and to be adjacent to one end of said gate electrode.

10. (Original) A semiconductor device according to claim 8, wherein said impurity region of the second conduction type is formed evenly in depth so as to be adjacent to one end of said gate electrode through said first gate oxide film and to surround the vicinity of said drain region.

Claims 11 to 13 canceled.